

Description

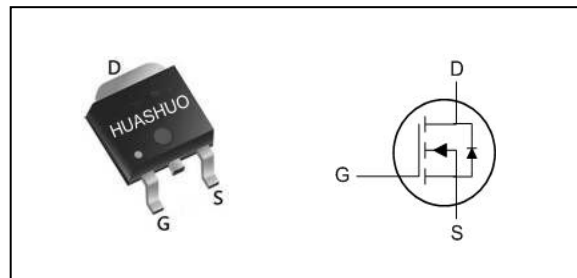
The HSU6048 is the high cell density trenched N-ch MOSFETs, which provide excellent R_{DS(on)} and gate charge for most of the synchronous buck converter applications.

The HSU6048 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V _{DS}	60	V
R _{DS(ON),TYP}	3.5	mΩ
I _D	90	A

TO-252 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	60	V
V _{GS}	Gate-Source Voltage	± 20	V
I _D @T _C =25°C	Continuous Drain Current ^{1,6}	90	A
I _D @T _C =100°C	Continuous Drain Current ^{1,6}	67	A
I _{DM}	Pulsed Drain Current ²	240	A
EAS	Single Pulse Avalanche Energy ³	101	mJ
I _{AS}	Avalanche Current	54	A
P _D @T _C =25°C	Total Power Dissipation ⁴	60	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹	---	60	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	1.8	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	60	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =20A	---	3.5	3.6	mΩ
		V _{GS} =4.5V , I _D =15A	---	4.7	5.4	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	---	2.3	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =48V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =48V , V _{GS} =0V , T _J =55°C	---	---	5	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ± 20V , V _{DS} =0V	---	---	± 100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V , I _D =20A	---	65	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	0.7	---	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =30V , V _{GS} =10V , I _D =20A	---	58	---	nC
Q _{gs}	Gate-Source Charge		---	16	---	
Q _{gd}	Gate-Drain Charge		---	4	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =30V , V _{GS} =10V , R _G =3Ω , I _D =20A	---	18	---	ns
T _r	Rise Time		---	8	---	
T _{d(off)}	Turn-Off Delay Time		---	50	---	
T _f	Fall Time		---	10.5	---	
C _{iss}	Input Capacitance	V _{DS} =30V , V _{GS} =0V , f=1MHz	---	3458	---	pF
C _{oss}	Output Capacitance		---	1522	---	
C _{rss}	Reverse Transfer Capacitance		---	22	---	

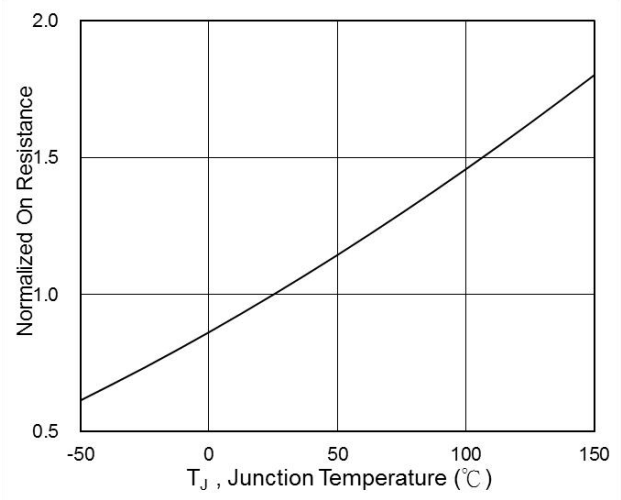
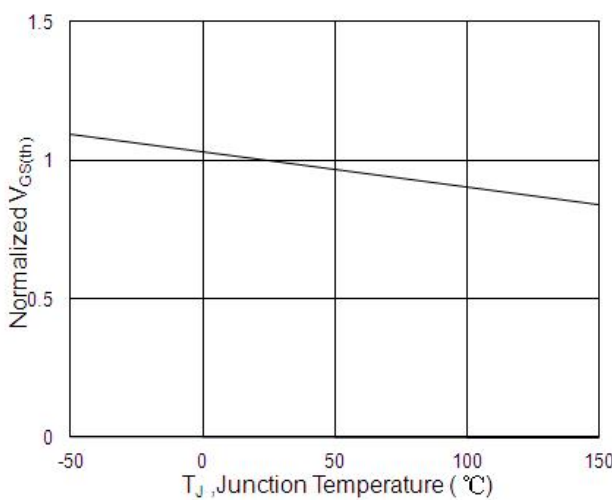
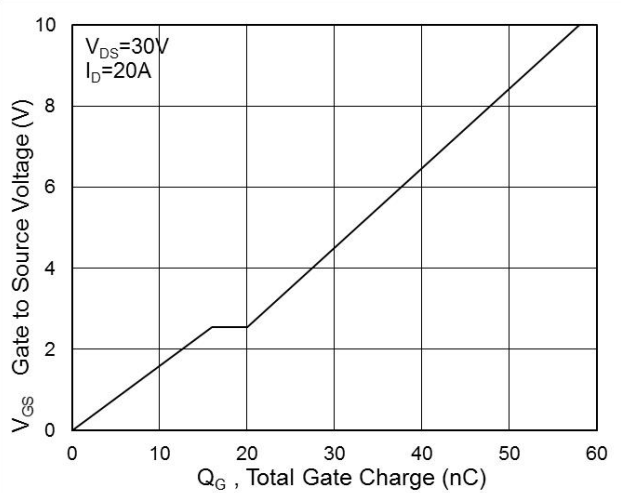
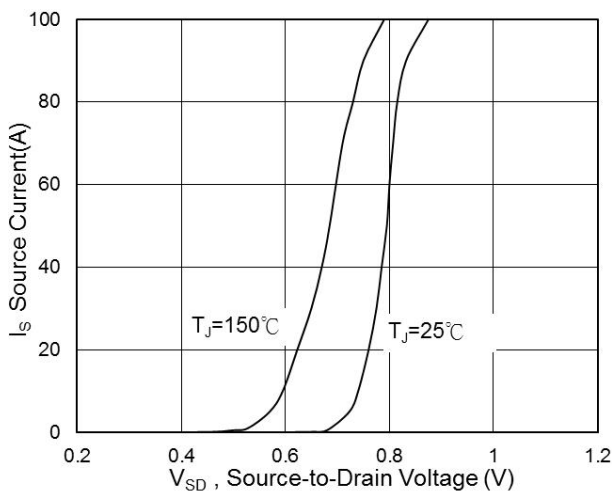
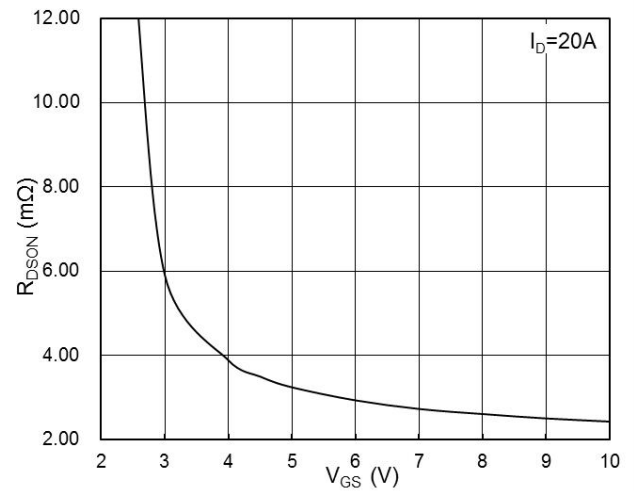
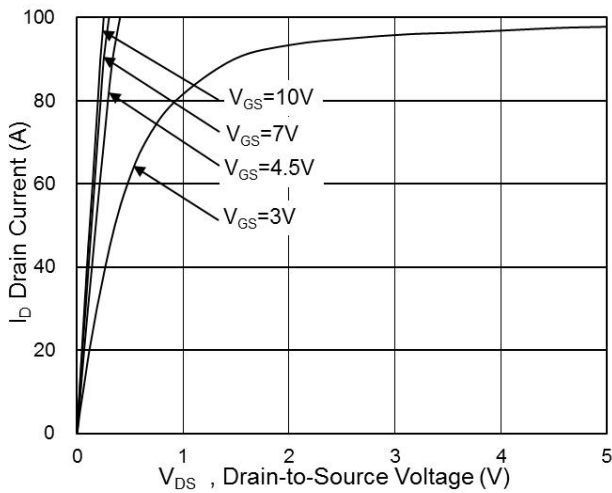
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	90	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =20A , dI/dt=100A/μs , T _J =25°C	---	24	---	nS
Q _{rr}	Reverse Recovery Charge		---	85	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=50V,V_{GS}=10V,L=0.1mH,I_{AS}=54A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.
- 6.The maximum current rating is package limited.

Typical Characteristics





N-Ch 60V Fast Switching MOSFETs

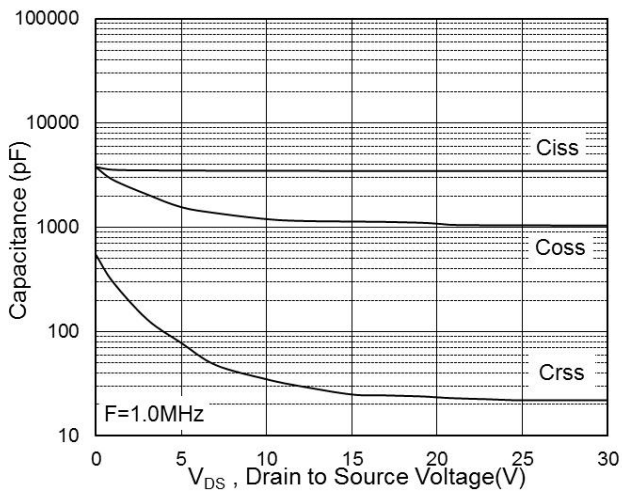


Fig.7 Capacitance

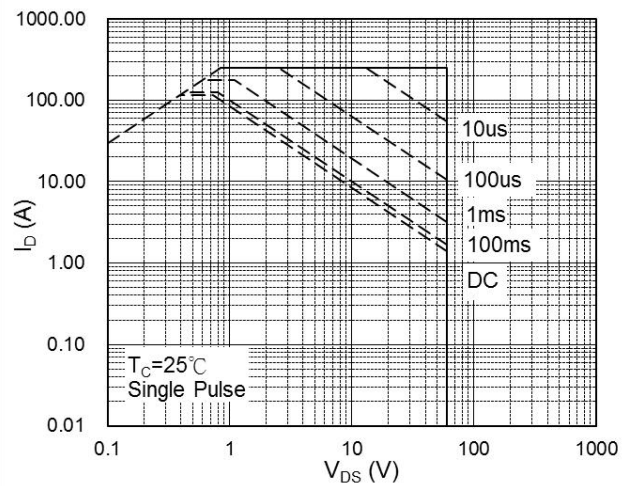


Fig.8 Safe Operating Area

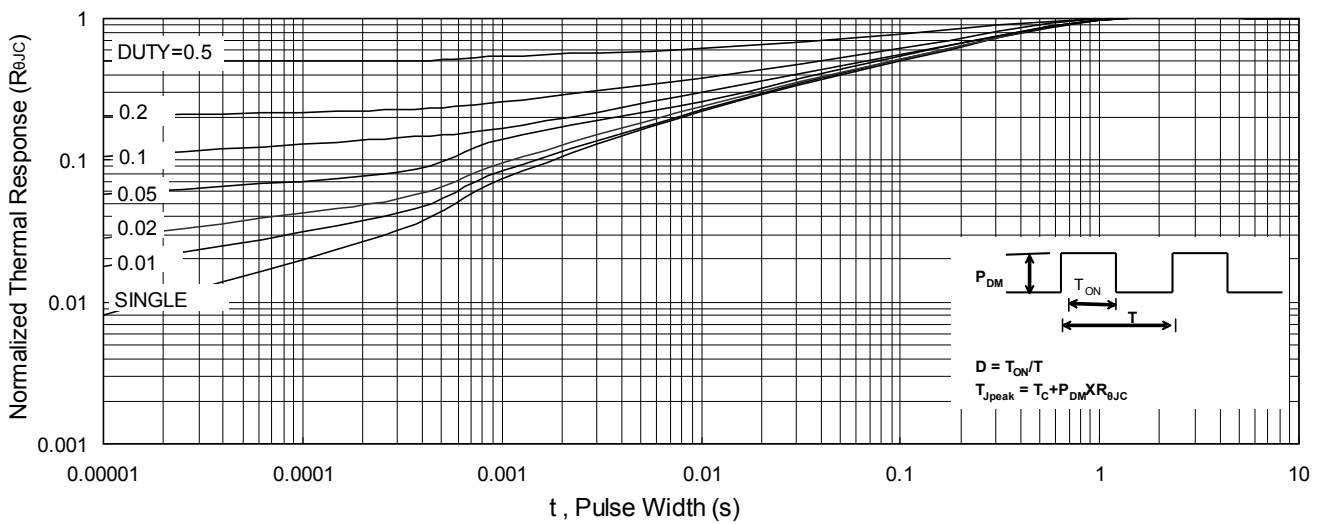


Fig.9 Normalized Maximum Transient Thermal Impedance

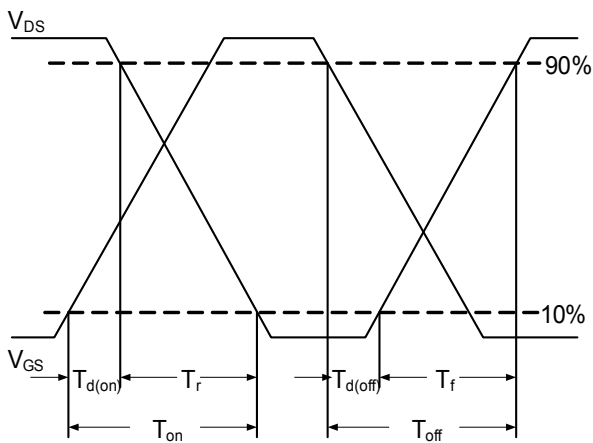


Fig.10 Switching Time Waveform

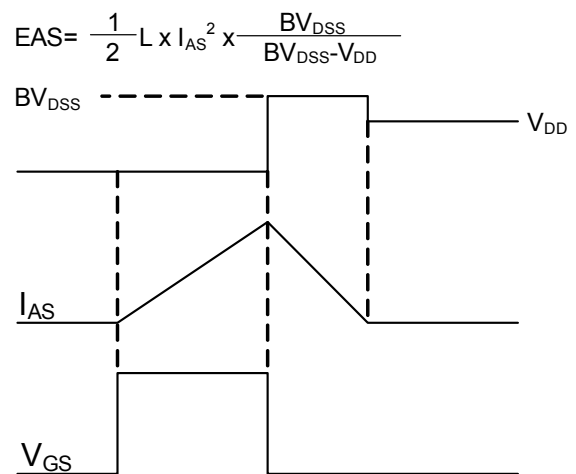
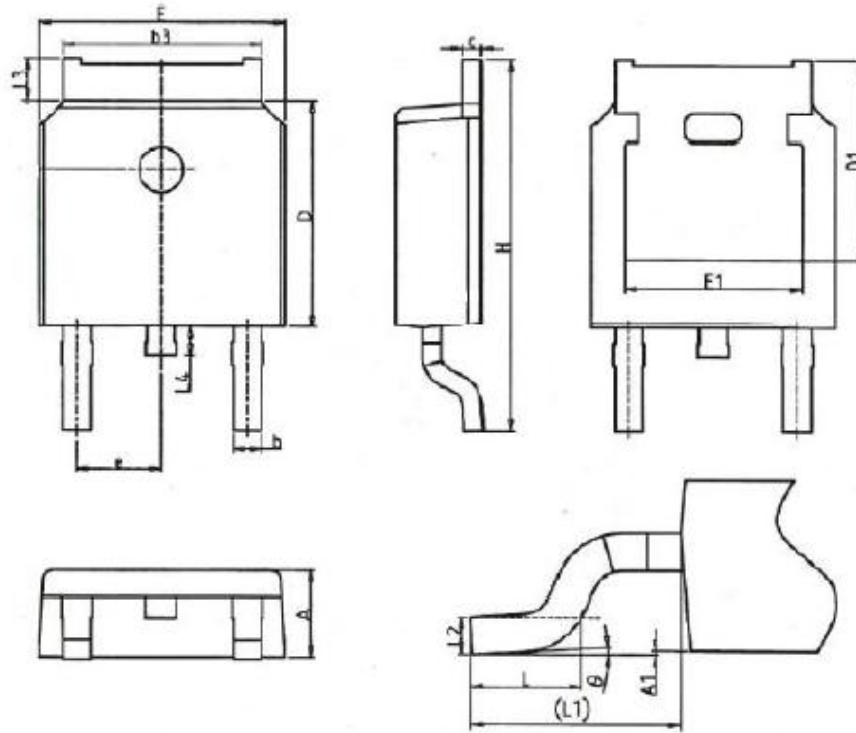


Fig.11 Unclamped Inductive Switching



TO252-2L Package Outline



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.18	2.40	0.086	0.095
A1	-	0.2	-	0.008
b	0.68	0.9	0.026	0.036
b3	4.95	5.46	0.194	0.215
c	0.43	0.89	0.017	0.035
D	5.97	6.22	0.235	0.245
D1	5.300REF		0.209REF	
E	6.35	6.73	0.250	0.265
E1	4.32	--	0.170	-
e	2.286BSC		0.09BSC	
H	9.4	10.5	0.370	0.413
L	1.38	1.78	0.054	0.070
L1	2.90REF		0.114REF	
L2	0.51BSC		0.020BSC	
L3	0.88	1.28	0.034	0.050
L4	0.5	1	0.019	0.039
θ	0°	8°	0°	8°

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